

We claim:

1. A method of making an electrically programmable memory element, comprising:

providing a first dielectric layer;

5 forming a conductive material over said first dielectric layer;

forming a second dielectric layer over said conductive material; and

10 forming a programmable resistance material in electrical contact with a peripheral surface of said conductive material.

2. The method of claim 1, wherein said peripheral surface is a sidewall surface of said conductive material.

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3. The method of claim 1, wherein said conductive material is at least one conductive sidewall spacer.

4. The method of claim 1, wherein said first dielectric layer  
20 includes a sidewall surface, said conductive material being formed over said sidewall surface.

5. The method of claim 4, wherein said peripheral surface of said conductive material is a top surface of said conductive material.

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6. The method of claim 1, wherein said peripheral surface is an edge of said conductive material.

7. The method of claim 1, wherein said programmable resistance  
5 material is a phase-change material.

8. The method of claim 1, wherein said programmable resistance material includes a chalcogen element.

10 9. The method of claim 1, wherein said first dielectric layer and said second dielectric layer are formed of the same material.